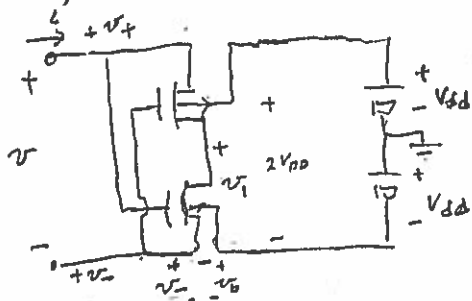


#1 a)



if  $v < 0$  both off

$$v_1 \equiv v/2, v_{BS}$$

if  $0 < v < V_{th}$  both off

if  $V_{th} < v$  need  $v_1 \Rightarrow$  by symmetry  $v_1 = v/2$

$$\Rightarrow v_{gs} = v, v_{gs} - V_{th} = v - V_{th} \text{ so } v/2 = v_{DS}$$

$\therefore$  saturation for  $v - V_{th} \leq v/2 \Rightarrow v/2 \leq V_{th} \Rightarrow v \leq 2V_{th}$

$\Rightarrow$  saturation for  $V_{th} \leq v \leq 2V_{th}$

$\Rightarrow$  ohmic for  $2V_{th} \leq v$

$$i = \begin{cases} 0 & v \leq V_{th} \\ k [2(v - V_{th})v/2 - (v/2)^2] (1 + 2v/2) & 2V_{th} \leq v \\ k \cdot (v - V_{th})^2 (1 + 2v/2) & V_{th} \leq v \leq 2V_{th} \end{cases} \quad \text{assume } V_{DD} \text{ large enough } \frac{1}{5} V$$

Or check substrate reversed bias

$$0 = -v_s + v_{gs_p} + v_{sb_p} + V_{DD} \quad \& \quad 0 = v_{gs_n} + v_{sb_n} - V_{DD}$$

$$\Rightarrow v_s = -v_{sb_p} - v_{gs_p} + V_{DD} \quad v_t = v_{gs_n} + v_{sb_n} - V_{DD}$$

$$v_+ - v_- = v = v + v_{sb_n} - V_{DD} - [-v - v_{sb_p} + V_{DD}] = 2v + (v_{sb_n} + v_{sb_p}) - 2V_{DD}$$

$$\Rightarrow 2V_{DD} = v + (v_{sb_n} + v_{sb_p}) = v + 2v_{sb_n} \text{ by symmetry}$$

$$\Rightarrow v_{sb_n} = V_{DD} - v/2 \geq 0 \text{ if } v < 2V_{DD} \Rightarrow \text{substrate diodes off}$$

c) assume  $M_n$  values from data.  $KP = 5.048 \times 10^{-5}$ ,  $V_{TO} = 0.8582$ ,  $\lambda = 0.0184$

check @  $v = 4V > 2V_{th} = 2 \times 0.8582 = 1.716 \Rightarrow i = 50 \mu A$  from Spice run

$$\text{from formula } i = \frac{5.048 \times 10^{-5} \times 10^{-5}}{2} [2(4 - 0.8582) \frac{4}{2} - (\frac{4}{2})^2] (1 + 0.0184 \times \frac{4}{2}) = 2.524 \times 10^{-5} [(4 \times 3 - 1418) - 4] (1.036) = 2.524 \times 10^{-5} \times 8.882 = 224.2 \times 10^{-6}$$

if use  $M_p$ ,  $KP = 1.908 \times 10^{-5}$ ,  $V_{TO} = -0.889271$ ,  $\lambda = 0.05012$

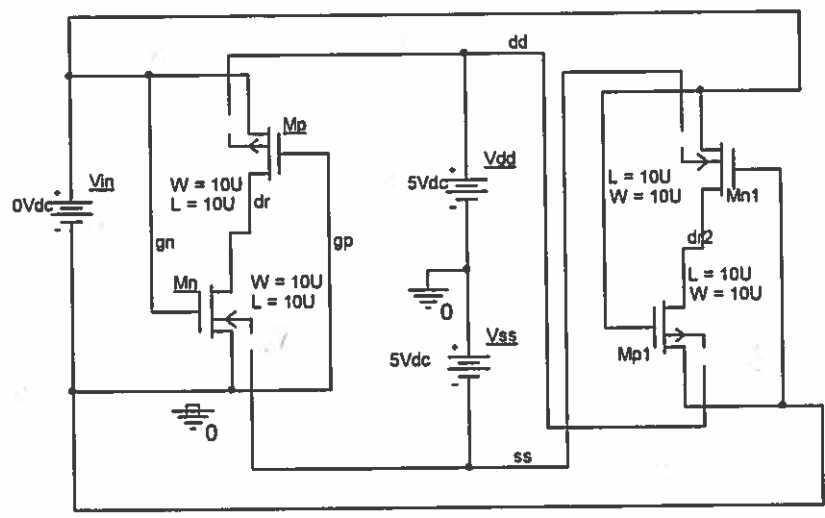
$$i = \frac{1.908 \times 10^{-5}}{2} [2(4 - 0.889) \frac{4}{2} - (\frac{4}{2})^2] (1 + 0.05012 \times 2) = 0.9635 \times 10^{-5} [4(2.111)] (1.1024) = 88.67 \times 10^{-6}$$

which is closer to 50  $\mu A$  of Spice; errors probably due to  $V_{th} \neq V_{TO}$  due to  $V_{SB}$  (but no  $\gamma$  is given for 4007)

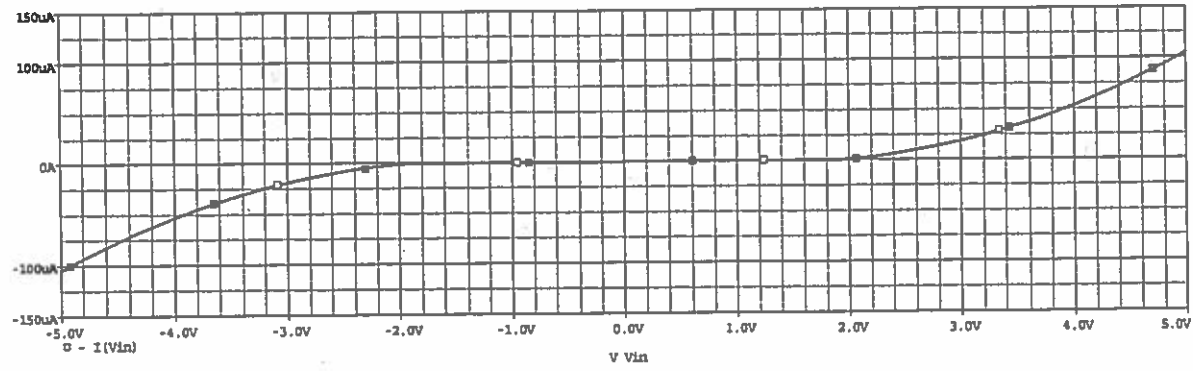
d) If the ground is attached to the bottom of  $M_n$  the source and drain of  $M_n$  are reversed when  $V_{in} < 0$  over when  $V_{in} > 0$  so the bulk-source diode of  $M_n$  becomes forward biased.

File g:/coursesF14/303H/final\_curve.doc

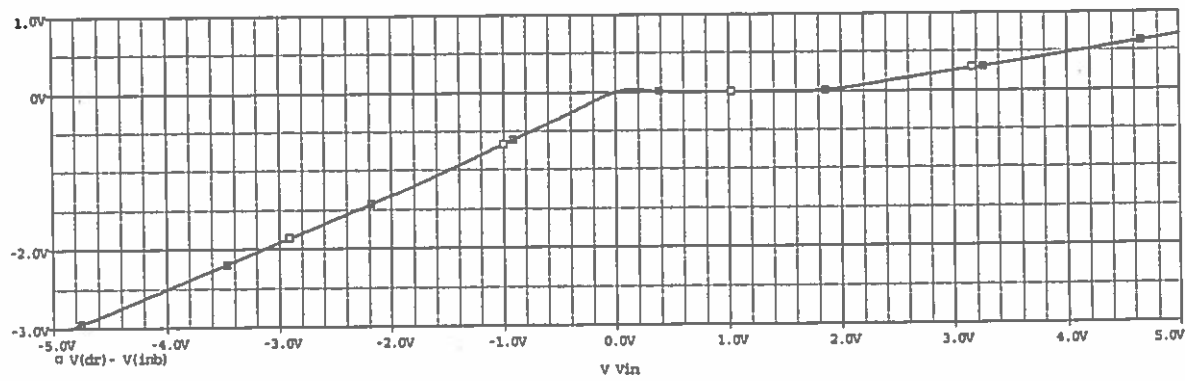
Circuit:



PSpice run for 303H final; above circuit: I vs v:



Vds for Mn:



#2

a) This is for the supply being one voltage source  $V_{dd}$  (w/ground) of large enough magnitude so both transistors are in saturation

b) For  $V_M$  including  $\lambda \neq 0$ , set  $I_{Dn} = I_{Sp}$  in saturation states

$$\beta_n (V_M - V_{tn})^2 (1 + \lambda V_M) = \beta_p (V_{dd} - V_M - |V_{tp}|)^2 (1 + \lambda [V_{dd} - V_M]) \Rightarrow \text{cubic in } V_M$$

$\Rightarrow$  can replace  $\beta_n$  by  $\beta_n (1 + \lambda V_M)$  &  $\beta_p$  by  $(1 + \lambda [V_{dd} - V_M])$

$$\Rightarrow \sqrt{\beta_n / \beta_p} \Rightarrow \sqrt{\frac{\beta_n (1 + \lambda V_M)}{\beta_p (1 + \lambda [V_{dd} - V_M])}} \approx \sqrt{\frac{\beta_n}{\beta_p}} \cdot \sqrt{(1 + \lambda V_M) (1 - \lambda [V_{dd} - V_M])}$$

$$\approx \sqrt{\frac{\beta_n}{\beta_p}} \cdot \sqrt{1 + \lambda [V_M - V_{dd} + V_M]} - (\text{ignore } \lambda^2 \text{ term})$$

$$\approx \sqrt{\frac{\beta_n}{\beta_p}} \cdot (1 - \frac{1}{2} \lambda V_{dd} + 2\lambda V_M) \approx \sqrt{\frac{\beta_n}{\beta_p}} (1 + \lambda \frac{V_{dd}}{2}) \text{ as } V_M \approx V_M|_{\lambda=0} \approx V_{dd}/2$$

$\Rightarrow$  improved  $V_M$

$$V_M = \frac{V_{dd} - |V_{tp}| + V_{tn} \cdot \sqrt{\frac{\beta_n}{\beta_p}} \cdot (1 + \frac{1}{2} \lambda V_{dd})}{1 + \sqrt{\frac{\beta_n}{\beta_p}} \cdot (1 + \frac{1}{2} \lambda V_{dd})}$$

$$c) \beta_n = \frac{\mu_n C_{ox} W}{L} = \frac{20.54 \times 10^{-6}}{2} \times \frac{144 \times 10^{-6}}{8 \times 10^{-6}} =$$

$$\beta_p = \frac{\mu_p C_{ox} W}{L} = \frac{10.32 \times 10^{-6}}{2} \times \frac{328 \times 10^{-6}}{8 \times 10^{-6}} =$$

$$\Rightarrow \frac{\beta_n}{\beta_p} = \frac{20.54 \times 144}{10.32 \times 328} = 0.8738 ; \sqrt{\beta_n / \beta_p} = 0.9348$$

$$V_{tn} = V_{T0} = 1.3, |V_{tp}| = |V_{T0p}| = 1.5 ; \lambda_n = 15 \times 10^{-3} = \lambda_p = \lambda$$

$$V_M|_{\lambda=0} = \frac{6 - 1.5 + 1.3 \times 0.9348}{1 + 0.9348} = \frac{5.7152}{1.9348} = 2.954$$

$$V_M|_{\lambda \neq 0} = \frac{6 - 1.5 + 1.3 \times 0.9348 \times (1 + 0.5 \times 15 \times 10^{-3} \times 6)}{1 + 0.9348 \times (1 + 0.5 \times 15 \times 10^{-3} \times 6)} = \frac{4.5 + 1.2152 \times (1.0075)}{1 + 0.9348 \times (1.0075)} \approx \frac{5.724}{1.942} = 2.947$$

$\therefore$  the Early effect only slightly changed  $V_M$  (case of  $V_M|_{\lambda=0}$  at  $\lambda=0$  gives  $V_M = 2.954$ )

#3. For the connection  $I = I_s e^{\frac{0}{V}} (1 - e^{-V/V_T}) = I_s (1 - e^{-V/V_T})$

a)  $g = \frac{dI}{dV} = I_s \left(-\left(-\frac{1}{V_T}\right)\right) e^{-V/V_T} = \frac{I_s}{V_T} e^{-V/V_T}$

when biased @  $V = V_b \Rightarrow g = \frac{I_s}{V_T} e^{-V_b/V_T}$

b) @  $V_b = 0.6$ ,  $I_s = 20 \times 10^{-18}$ ,  $V_T = 0.026 \Rightarrow V_b/V_T = \frac{0.6 \times 10^{-1}}{0.026 \times 10^{-1}} = 23.077$

$e^{-V_b/V_T} = 9.502 \times 10^{-11}$ ,  $I_s/V_T = \frac{20 \times 10^{-18}}{26 \times 10^{-3}} = 7.692 \times 10^{-16}$

$\therefore g = 7.692 \times 9.502 \times 10^{-16} \times 10^{-11} = 7.309 \times 10^{-26}$

$\Rightarrow r = \frac{1}{g} = \frac{10^{26}}{7.309} = \frac{10}{7.309} \times 10^{25} = 1.368 \times 10^{25} \Rightarrow \text{very large!}$

c) If  $V < 0$  the substrate diode is forward biased in which case large currents flow  $\Rightarrow$  small  $r$